

**isc N-Channel MOSFET Transistor****IPP039N04L, IIPP039N04L****• FEATURES**

- Static drain-source on-resistance:  
 $R_{DS(on)} \leq 3.9m\Omega$
- Enhancement mode
- Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**• DESCRIPTION**

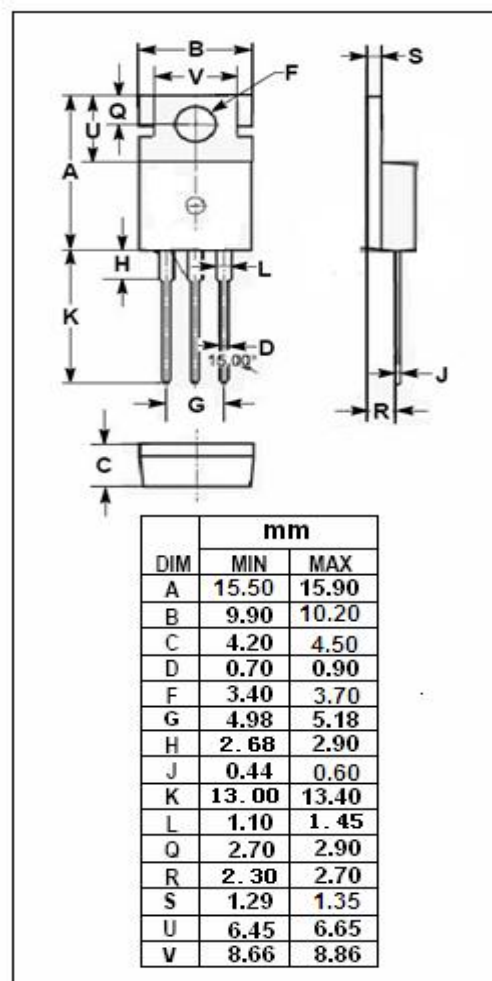
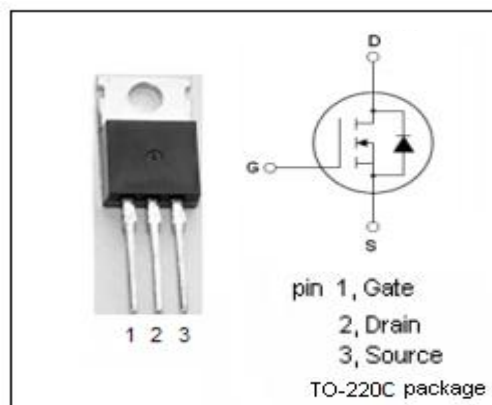
- Fast switching for SMPS
- Optimized technology for DC/DC converters

**• ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

| SYMBOL    | PARAMETER                                  | VALUE    | UNIT             |
|-----------|--|----------|------------------|
| $V_{DS}$  | Drain-Source Voltage                       | 40       | V                |
| $V_{GS}$  | Gate-Source Voltage                        | $\pm 20$ | V                |
| $I_D$     | Drain Current-Continuous                   | 80       | A                |
| $I_{DM}$  | Drain Current-Single Pulsed                | 400      | A                |
| $P_D$     | Total Dissipation @ $T_c=25^\circ\text{C}$ | 94       | W                |
| $T_j$     | Max. Operating Junction Temperature        | 175      | $^\circ\text{C}$ |
| $T_{stg}$ | Storage Temperature                        | -55~175  | $^\circ\text{C}$ |

**• THERMAL CHARACTERISTICS**

| SYMBOL         | PARAMETER                             | MAX | UNIT               |
|----------------|---------------------------------------|-----|--------------------|
| $R_{th(ch-c)}$ | Channel-to-case thermal resistance    | 1.6 | $^\circ\text{C/W}$ |
| $R_{th(ch-a)}$ | Channel-to-ambient thermal resistance | 62  | $^\circ\text{C/W}$ |



**isc N-Channel MOSFET Transistor****IPP039N04L, IPP039N04L****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

| SYMBOL       | PARAMETER                      | CONDITIONS                              | MIN | TYP | MAX | UNIT             |
|--------------|--------------------------------|---|-----|-----|-----|------------------|
| $BV_{DSS}$   | Drain-Source Breakdown Voltage | $V_{GS}=0V$ ; $I_D = 1\text{mA}$        | 40  |     |     | V                |
| $V_{GS(th)}$ | Gate Threshold Voltage         | $V_{DS}=V_{GS}$ ; $I_D=45\ \mu\text{A}$ | 1.2 |     | 2   | V                |
| $R_{DS(on)}$ | Drain-Source On-Resistance     | $V_{GS}=10V$ ; $I_D=80\text{A}$         |     |     | 3.9 | $\text{m}\Omega$ |
| $I_{GSS}$    | Gate-Source Leakage Current    | $V_{GS}=20V$ ; $V_{DS}=0V$              |     |     | 100 | nA               |
| $I_{DSS}$    | Drain-Source Leakage Current   | $V_{DS}=40V$ ; $V_{GS}=0V$              |     |     | 1   | $\mu\text{A}$    |
| $V_{SD}$     | Diode forward voltage          | $I_F=80\text{A}$ ; $V_{GS}=0V$          |     |     | 1.2 | V                |

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